



**USG10R068H**

Preliminary

**POWER MOSFET**

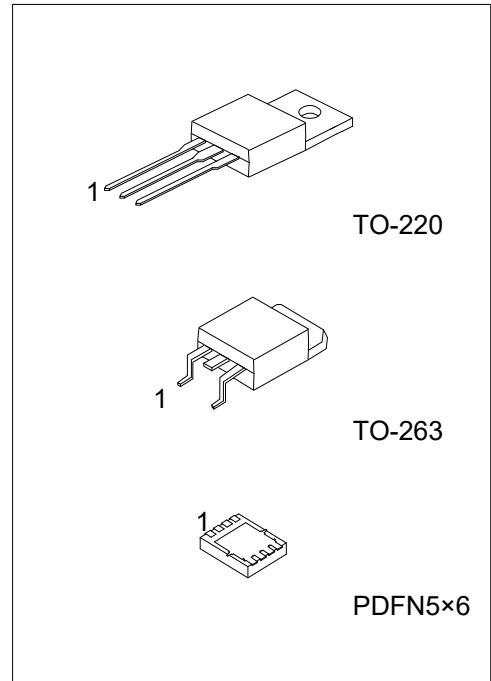
QW-R209-523.a N-CHANNEL SGT  
ENHANCEMENT POWER  
MOSFET

■ DESCRIPTION

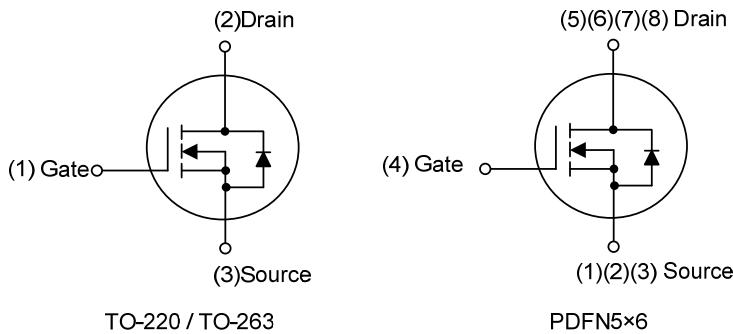
The UTC **USG10R068H** is a N-channel Power MOSFET, it uses UTC's advanced technology to provide the customers with low  $R_{DS(ON)}$  characteristic by high cell density trench technology.

■ FEATURES

- \*  $R_{DS(ON)} \leq 6.8 \text{ m}\Omega @ V_{GS}=10V, I_D=35A$
- \* Extremely low on-resistance  $R_{DS(ON)}$
- \* Excellent Low Ciss



■ SYMBOL



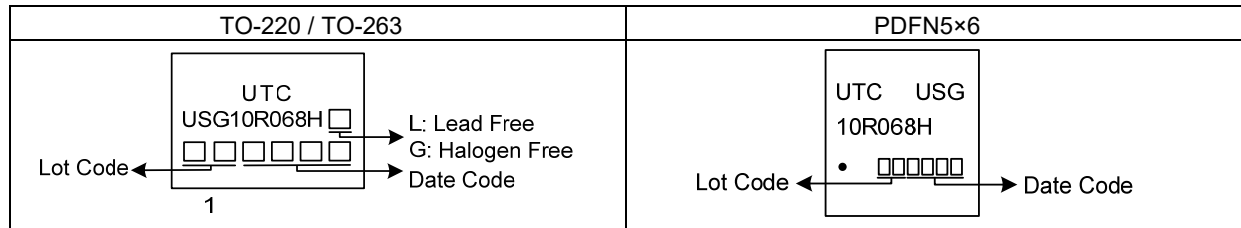
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment								Packing
Lead Free	Halogen Free		1	2	3	4	5	6	7	8	
USG10R068HL-TA3-T	USG10R068HG-TA3-T	TO-220	G	D	S	-	-	-	-	-	Tube
USG10R068HL-TQ2-T	USG10R068HG-TQ2-T	TO-263	G	D	S	-	-	-	-	-	Tube
USG10R068HL-TQ2-R	USG10R068HG-TQ2-R	TO-263	G	D	S	-	-	-	-	-	Tape Reel
USG10R068HL-P5060-R	USG10R068HG-P5060-R	PDFN5x6	S	S	S	G	D	D	D	D	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>USG10R068HG-TA3-T</p> <p>(1)Packing Type</p> <p>(2)Package Type</p> <p>(3)Green Package</p>	<p>(1) T: Tube, R: Tape Reel</p> <p>(2) TA3: TO-220, TQ2: TO-263, P5060: PDFN5x6</p> <p>(3) G: Halogen Free and Lead Free, L: Lead Free</p>
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### MARKING



■ ABSOLUTE MAXIMUM RATING ( $T_C=25^{\circ}\text{C}$  unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT	
Drain-Source Voltage	$V_{DSS}$	100	V	
Gate-Source Voltage	$V_{GSS}$	$\pm 20$	V	
Drain Current	DC	$I_D$	90	A
	Pulsed (Note 2)	$I_{DM}$	180	A
Avalanche Energy	Single Pulsed (Note 3)	$E_{AS}$	14.5	mJ
Peak Diode Recovery dv/dt (Note 4)	dv/dt	3.6	V/ns	
Power Dissipation	TO-220/TO-263	$P_D$	119	W
	PDFN5x6		53	W
Junction Temperature	$T_J$	+150	$^{\circ}\text{C}$	
Storage Temperature Range	$T_{STG}$	-55 ~ +150	$^{\circ}\text{C}$	

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature

3.  $L = 0.1\text{mH}$ ,  $I_{AS} = 17\text{A}$ ,  $V_{DD} = 50\text{V}$ ,  $R_G = 25\ \Omega$ , Starting  $T_J = 25^{\circ}\text{C}$

4.  $I_{SD} \leq 30\text{A}$ ,  $di/dt \leq 200\text{A}/\mu\text{s}$ ,  $V_{DD} \leq V_{(BR)DSS}$ ,  $T_J \leq 25^{\circ}\text{C}$

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT	
Junction to Ambient	TO-220/TO-263	$\theta_{JA}$	62.5	$^{\circ}\text{C}/\text{W}$
	PDFN5x6		65 (Note)	$^{\circ}\text{C}/\text{W}$
Junction to Case	TO-220/TO-263	$\theta_{JC}$	1.05	$^{\circ}\text{C}/\text{W}$
	PDFN5x6		2.36 (Note)	$^{\circ}\text{C}/\text{W}$

Note: Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

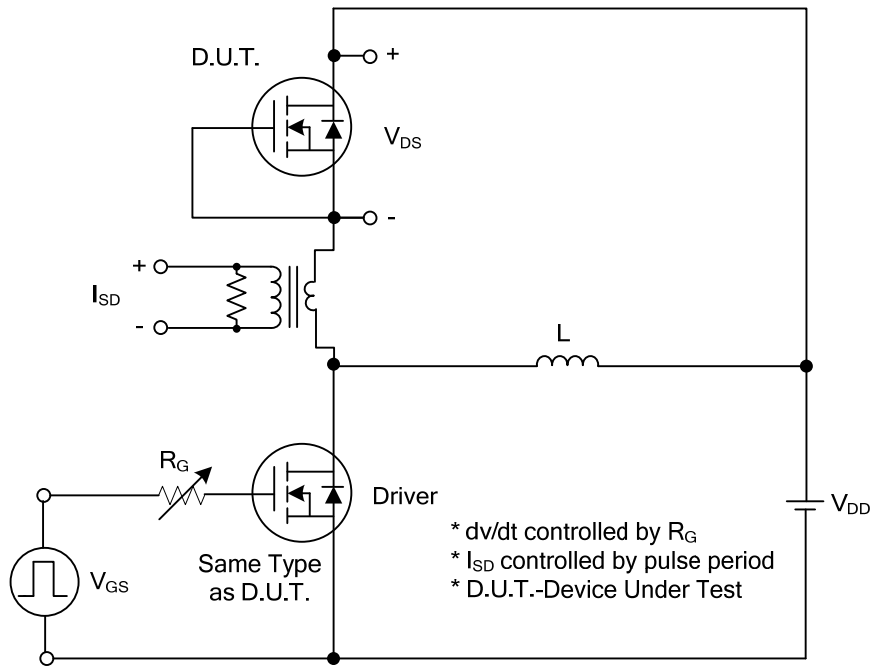
■ ELECTRICAL CHARACTERISTICS (T<sub>A</sub>=25°C unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	100			V
Drain-Source Leakage Current	I <sub>DSS</sub>	V <sub>DS</sub> =100V, V <sub>GS</sub> =0V			1	μA
Gate-Source Leakage Current	Forward	I <sub>GSS</sub> V <sub>GS</sub> =+20V, V <sub>DS</sub> =0V			+100	nA
	Reverse		V <sub>GS</sub> =-20V, V <sub>DS</sub> =0V			-100
<b>ON CHARACTERISTICS</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	2.0		4.0	V
Static Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =35A			6.8	mΩ
<b>DYNAMIC PARAMETERS</b>						
Input Capacitance	C <sub>ISS</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> =25V, f=1.0MHz		2579		pF
Output Capacitance	C <sub>OSS</sub>			1415		pF
Reverse Transfer Capacitance	C <sub>RSS</sub>			164		pF
<b>SWITCHING PARAMETERS</b>						
Total Gate Charge	Q <sub>G</sub>	V <sub>DS</sub> =80V, V <sub>GS</sub> =10V, I <sub>D</sub> =90A (Note 1, 2)		62		nC
Gate to Source Charge	Q <sub>GS</sub>			11		nC
Gate to Drain Charge	Q <sub>GD</sub>			25		nC
Turn-ON Delay Time	t <sub>D(ON)</sub>	V <sub>DD</sub> =50V, V <sub>GS</sub> =10V, I <sub>D</sub> =90A, R <sub>G</sub> =3Ω (Note 1, 2)		13		ns
Rise Time	t <sub>r</sub>			19		ns
Turn-OFF Delay Time	t <sub>D(OFF)</sub>			34		ns
Fall-Time	t <sub>f</sub>			21		ns
<b>SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS</b>						
Maximum Continuous Drain-Source Diode Forward Current	I <sub>S</sub>				90	A
Maximum Pulsed Drain-Source Diode Forward Current	I <sub>SM</sub>				180	A
Diode Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> =90A, V <sub>GS</sub> =0V			1.4	V
Reverse Recovery Time (Note 1)	t <sub>rr</sub>	I <sub>S</sub> =30A, V <sub>GS</sub> =0V, dI <sub>F</sub> /dt = 100A/μs		58		nS
Reverse Recovery Charge	Q <sub>rr</sub>				112	

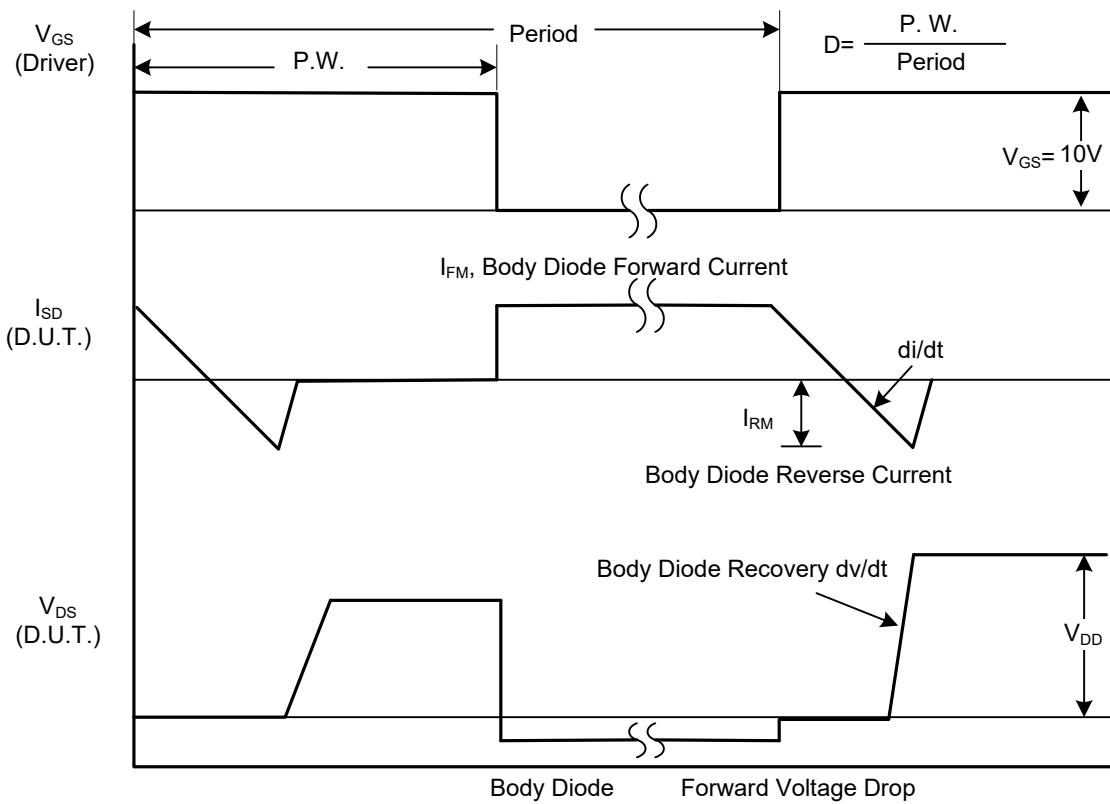
Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

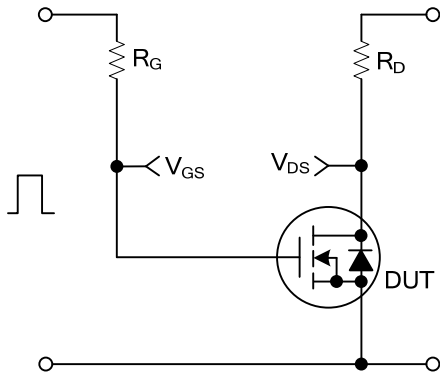


Peak Diode Recovery  $dv/dt$  Test Circuit

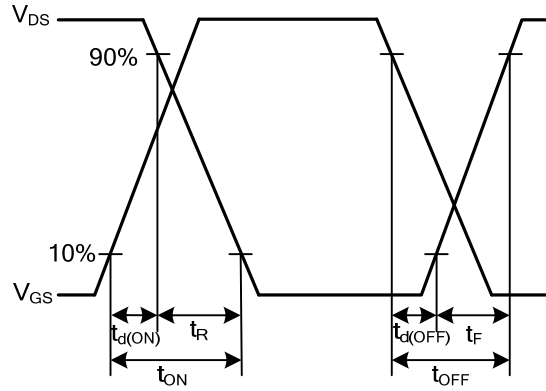


Peak Diode Recovery  $dv/dt$  Waveforms

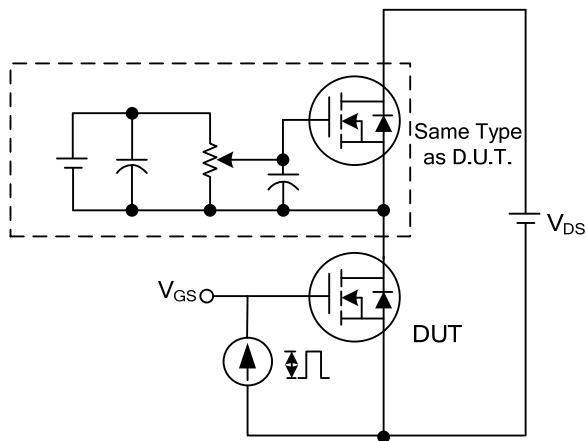
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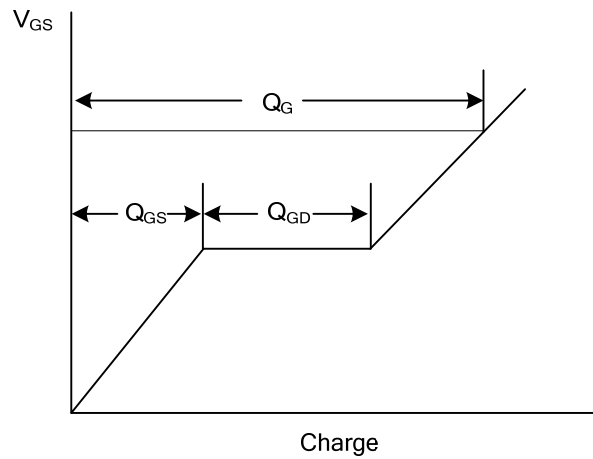
Switching Test Circuit



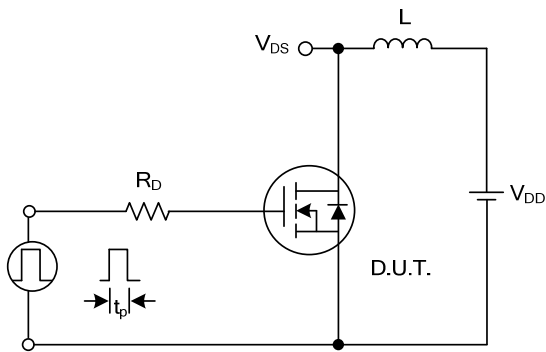
Switching Waveforms



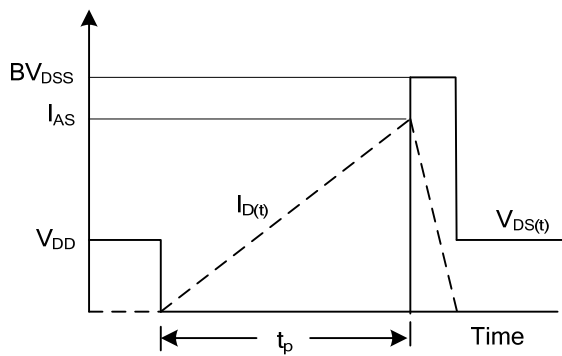
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

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